WHAT IS CLAIMED IS:

1. A semiconductor device comprising a plurality of wirings or conductive film patterns formed with a clearance between the wirings or the conductive film patterns on a semiconductor substrate, wherein:

a protrusion is formed at a corner or an end part of at least one of the wirings or the conductive film patterns and the protrusion faces the clearance.

2. The semiconductor device according to claim 1, wherein the protrusion protrudes outward from the corner.

3. The semiconductor device according to claim 1, wherein the protrusion is an inward extension bridging a corner portion.

4. The semiconductor device according to claim 1, wherein the conductive film patterns are provided with a T-shaped groove or a cross-shaped groove for separating the patterns, and a protrusion is formed at a corner of at least one of the conductive film patterns positioned at a crossing of the respective grooves constituting the T-shaped groove or the cross-shaped groove.

5. The semiconductor device according to claim 1, wherein the wirings including a first wiring and a second wiring are formed in substantially parallel with a predetermined spacing on the semiconductor substrate, an end part of the second wiring is positioned along the first wiring, and

at least one protrusion is formed at the end part of the second wiring so as to protrude toward the first wiring, or at least one protrusion is formed at a side of the first wiring that faces the end part of the second wiring so as to protrude toward the second wiring.

6. The semiconductor device according to claim 1, wherein the semiconductor substrate is provided further with a bonding pad made of the same film as the wirings, and the wirings and the bonding pad are coated with an insulating protective film having an aperture to expose the bonding pad.

7. The semiconductor device according to claim 1, wherein the semiconductor substrate is provided further with a bonding pad made of the same film as the conductive patterns, and the patterns and the bonding pad are coated with an

insulating protective film having an aperture to expose the bonding pad.

8. The semiconductor device according to claim 5, wherein the semiconductor substrate is provided further with a bonding pad made of the same film as the first and second wirings, and the wirings and the bonding pad are coated with an insulating protective film having an aperture to expose the bonding pad.

9. The semiconductor device according to claim 1, wherein the protrusion has an area ranging from 0.2 μm^2 to 3.0 μm^2.

10. The semiconductor device according to claim 1, wherein an insulating protective film is further provided on the clearance between the wirings or on the conductive film patterns, and the insulating protective film is contacted as a whole with the clearance between the wirings or the surface of the conductive film patterns.

11. A method of manufacturing a semiconductor device comprising a plurality of wirings or conductive film patterns formed on a clearance between the wirings or on the conductive film patterns on a semiconductor substrate, wherein:
a protrusion is formed at a corner or an end part of at least one of the wirings or the conductive film patterns and the protrusion faces the clearance between the wirings or the conductive film patterns.

12. The method of manufacturing a semiconductor device according to claim 11, wherein the method comprises:

forming, on the semiconductor substrate, a bonding pad made of the same film as the wirings or the conductive film patterns,

forming an insulating protective film for covering the wirings, the conductive film patterns and the bonding pad,

forming a patterned photosensitive resin film on the insulating protective film, and

etching selectively the insulating protective film by using the photosensitive resin film as a mask, thereby forming an aperture in the insulating protective film to expose the bonding pad.

13. The method of manufacturing a semiconductor device according to claim 11, wherein the protrusion protrudes outward to the corner.

14. The method of manufacturing a semiconductor device according to claim 11, wherein the protrusion is an inward extension bridging a corner portion.

15. The method of manufacturing a semiconductor device according to claim 11, wherein the conductive film patterns are provided with a T-shaped groove or a cross-shaped groove for separating the patterns, and a protrusion is formed at a corner of at least one of the conductive film patterns positioned at a crossing of the respective grooves constituting the T-shaped groove or the cross-shaped groove.

16. The method of manufacturing a semiconductor device according to claim 11, wherein the wirings including a first wiring and a second wiring are formed in substantially parallel at a predetermined spacing on the semiconductor substrate, an end part of the second wiring is positioned along the first wiring,

at least one protrusion is formed at the end part of the second wiring so as to protrude toward the first wiring, or at least one protrusion is formed at a side of the first wiring that faces the end part of the second wiring so as to protrude toward the second wiring.

17. The method of manufacturing a semiconductor device according to claim 11, wherein the protrusion has an area ranging from 0.2 μm^2 to 3.0 μm^2.

18. The method of manufacturing a semiconductor device according to claim 12, wherein an insulating protective film is further provided on the clearance between the wirings or on the conductive film patterns, and the insulating protective film is contacted as a whole with the clearance between the wirings or the surface of the conductive film patterns.